## / Descriptions

TO-252

Ultrafast Recovery Diode in a TO-252 Plastic Package.

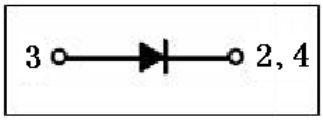
## / Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

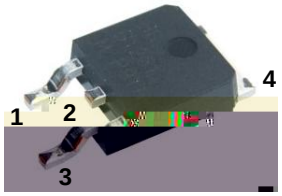
## / Applications

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

## / Equivalent Circuit




## / Pinning




PIN1 NC PIN 2 Cathode PIN 3 Anode PIN 4:Case

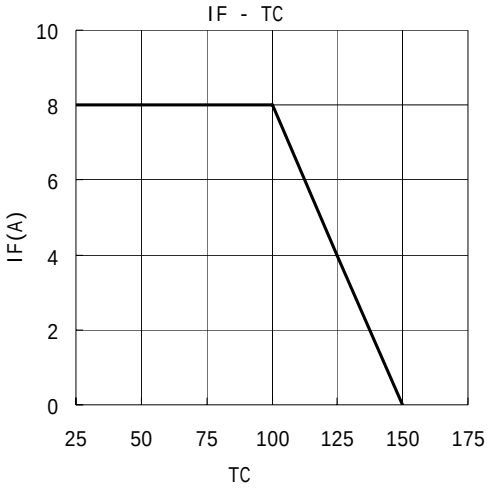
## / $h_{FE}$ Classifications & Marking

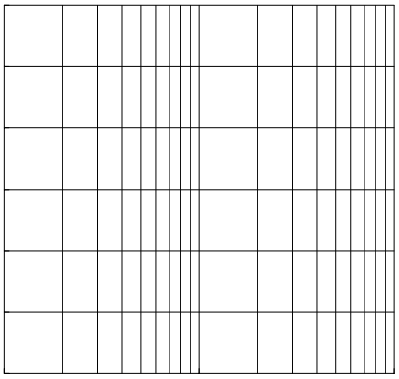
See Marking Instructions.

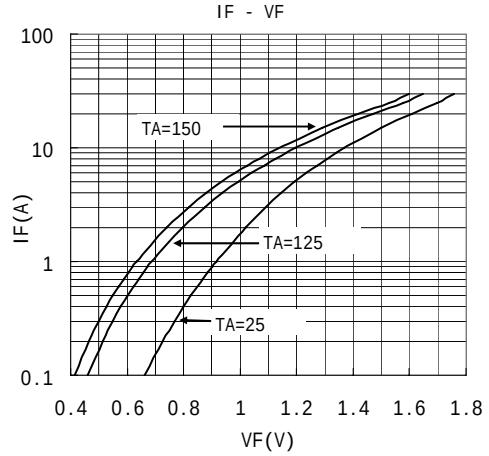
| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Peak Repetitive Reverse Voltage | $V_{RRM}$ | 600 | V |
| Working Peak Reverse Voltage | $V_{RMS}$ | 420 | V |
| Average Rectified Forward Current | $I_F$ | 8 | A |
| Non Repetitive Peak Surge Current | $I_{FSM}$ | 125 | A |
| Thermal resistance, junction to case | $R_{Jc}$ | 3.5 | /W |
| Junction and Storage Temperature Range | $T_j$ $T_{stg}$ | -55 150 | |

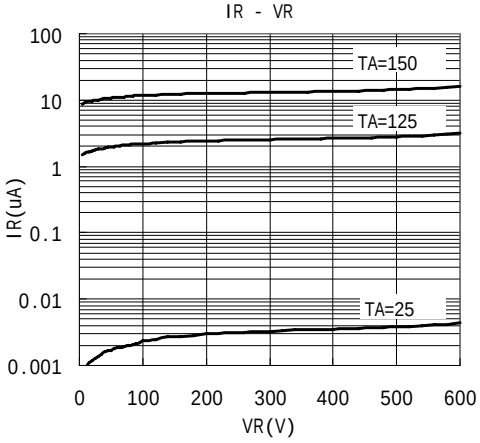
| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Reverse Voltage | $V_{BR}$ | $I_R$=100uA | 600 | | | V |
| | | $I_F$=8A Tc=25 | | 1.4 | 1.7 | V |
| Forward Voltage | $V_F$ | $I_F$=16A Tc=25 | | 1.7 | 2.1 | V |
| 1.4 1.7 | | I=16A Tc1=25 | | | | |

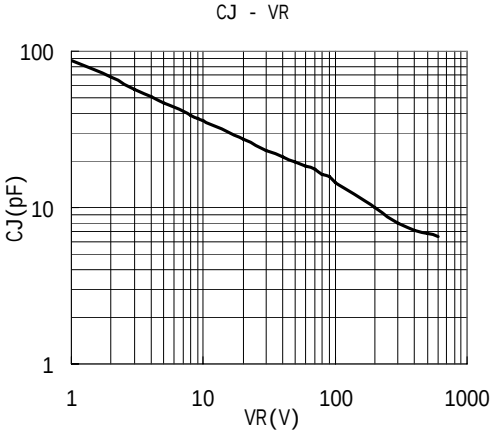
## / Electrical Characteristic Curve



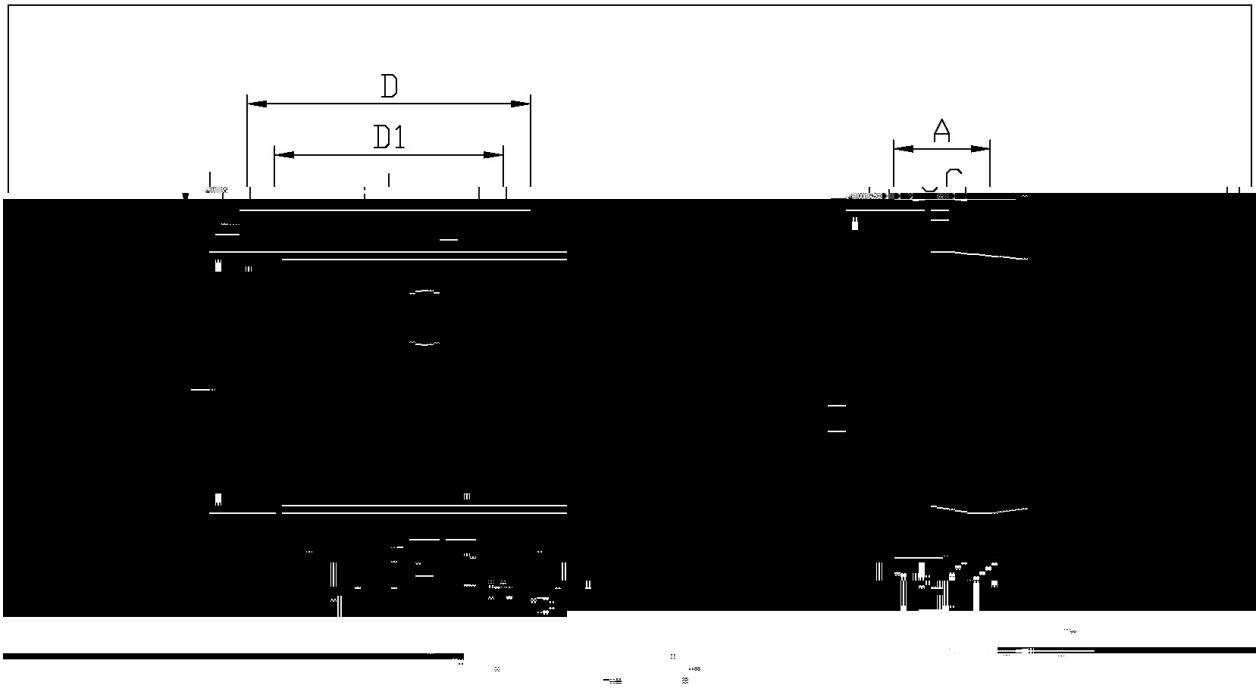





## / Package Dimensions




| | | | | |
|---|---|---|---|---|
| 00 | 0.10 | D1 | 5.10 | 5.50 | K | 0. |

TO-252

## / Marking Instructions




BR

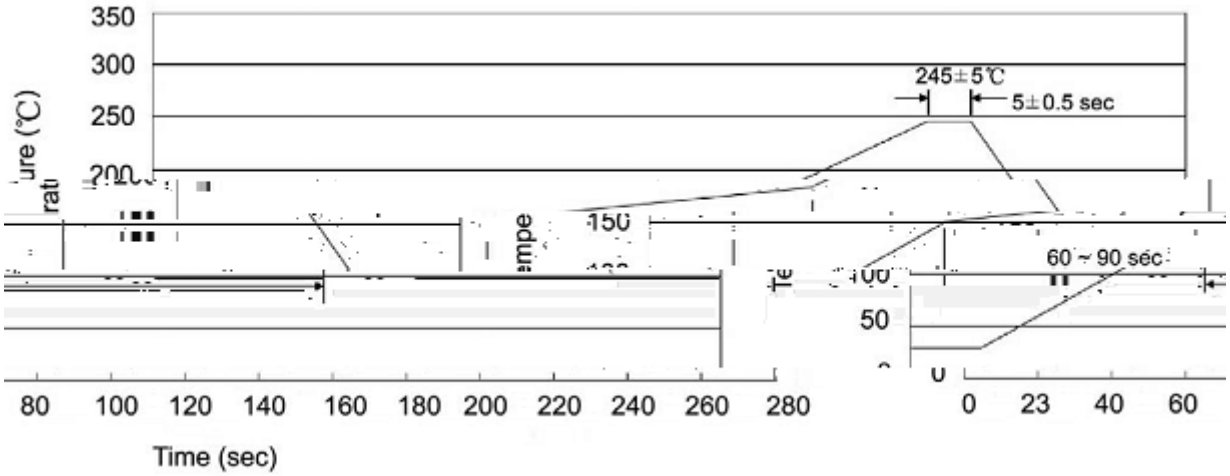
MUR860

****

Note:

| | |
|---|---|
| BR: | Company Code |
| MUR860 | Product Type. |
| ****: | Lot No. Code, code change with Lot No. |

## ( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

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